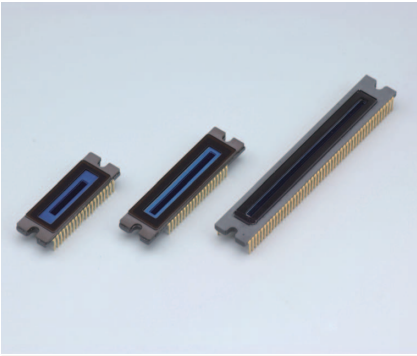


TDI-CCD image sensors



S10200-02-01 S10201-04-01 S10202-08-01 S10202-16-01

Operating the back-thinned CCD in TDI mode delivers high sensitivity.

TDI-CCD image sensors capture clear and bright images even under low-light-level conditions. During TDI (time delay integration) mode, the CCD captures an image of a moving object while transferring integrated signal charges synchronously with the object movement. This operation mode dramatically boosts sensitivity to high levels even when capturing fast moving objects. Our new TDI-CCD uses the back-thinned structure to achieve even higher quantum efficiency over a wide spectral range from UV to near IR region (200 to 1100 nm).

Features

- TDI mode gives high sensitivity
- High-speed, continuous image acquisition
- Back-thinned structure ensures high sensitivity from UV to near IR
- Multiple ports for high-speed line rate
- Low noise

Applications

- Sequential imaging of high-speed moving samples
- Inspection tasks on electronic parts production line
- Semiconductor inspection
- Flow cytometry

TDI mode

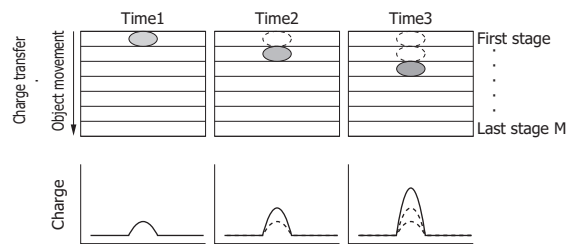
In FFT-CCD, signal charges in each line are vertically transferred during charge readout. TDI mode synchronizes this vertical transfer timing with the movement of the object, so that signal charges are integrated a number of times equal to the number of vertical stages of the CCD pixels. In the TDI mode, the signal charges must be transferred in the same direction at the same speed as those of the object to be imaged. These speeds are expressed by the following equation:

$$v = f \times d$$

v: object moving speed, charge transfer speed, f: vertical transfer frequency, d: pixel size

In the right figure, when the first stage charges are transferred to the second stage, an additional charges are produced in the second stage by photoelectric conversion and accumulated. When this operation is continuously repeated until reaching the last stage M (the number of vertical stages), signal charges which are M times greater than the initial charges are accumulated. Since the signal charges on each line are output from the CCD horizontal shift register, a two-dimensional image can be continuously acquired. In this way the TDI mode achieves sensitivity which is M times higher than linear image sensors (S/N is improved \sqrt{M} times). The TDI mode also improves sensitivity variations compared to frame mode operation.

☑ Schematic diagram showing integrated exposure by TDI mode



KMPDC0139EA

Selection guide

Type no.	Number of total pixels (H × V)	Number of effective pixels (H × V)	Number of ports	Pixel rate (MHz/port)	Line rate (kHz)	Vertical transfer	Applicable*1 camera
S10200-02-01*2*3	1040 × 128	1024 × 128	2	30	50	Bi-directional	-
S10201-04-01*2*3	2080 × 128	2048 × 128	4				C10000-801/-A01
S10202-08-01	4160 × 128	4096 × 128	8		-		
S10202-16-01	4224 × 128	4096 × 128	16		100		-

*1: The C10000 series cameras are products manufactured by Hamamatsu Photonics, System Division (refer to page 14).

*2: Temporary window type (S10200-02N-01, S10201-04N-01) is also available upon request.

*3: Light-shield mask type (S10200-02M-01, S10201-04M-01) for horizontal register shielding is also available upon request [see device structure (P.7)]. The light-shield mask's aperture size in the vertical direction is 96 pixels. The effect of the light-shield mask may vary depending on the wavelength of the light source in use and the incident angle of light.

Structure

Parameter	Specification
Pixel size (H × V)	12 × 12 μm
TDI stage	128
Anti-blooming	FW × 100 (min.)
Vertical clock	3 phases
Horizontal clock	2 phases
Output circuit	Three-stage MOSFET source follower
Package	Ceramic DIP (refer to dimensional outlines)
Window	Quartz glass*4

*4: Resin sealing

Absolute maximum ratings (Ta=25 °C)

Parameter	Symbol	Min.	Typ.	Max.	Unit
Operating temperature*5 *6 *7	Topr	-50	-	60	°C
Storage temperature*7	Tstg	-50	-	70	°C
Output transistor drain voltage	VOD	-0.5	-	25	V
Reset drain voltage	VRD	-0.5	-	18	V
Overflow drain voltage	VOFD	-0.5	-	18	V
Overflow gate voltage	VOFG	-10	-	15	V
Summing gate voltage	VSG	-10	-	15	V
Output gate voltage	VOG	-10	-	15	V
Reset gate voltage	VRG	-10	-	15	V
Transfer gate voltage	VTG	-10	-	15	V
Vertical clock voltage	VP1V, VP2V, VP3V	-8	-	+8	V
Horizontal clock voltage	VP1H, VP2H	-10	-	15	V

*5: Package temperature

*6: The chip temperature may increase due to heating in high-speed operation. We recommend taking measures to dissipate heat as needed.

*7: No dew condensation

When there is a temperature difference between a product and the surrounding area in high humidity environment, dew condensation may occur on the product surface. Dew condensation on the product may cause deterioration in characteristics and reliability.

Note: Exceeding the absolute maximum ratings even momentarily may cause a drop in product quality. Always be sure to use the product within the absolute maximum ratings.

Operating conditions (TDI mode, Ta=25 °C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	
Output transistor drain voltage	VOD	12	15	18	V	
Reset drain voltage	VRD	12	14	16	V	
Output gate voltage	VOG	4	6	8	V	
Substrate voltage	VDGND, VAGND	-	0	-	V	
Overflow drain voltage	VOFD	7	9	11	V	
Overflow gate voltage	VOFG	3	5	7	V	
Vertical shift register clock voltage	High	VP1VH, VP2VH, VP3VH	4	6	8	V
	Low	VP1VL, VP2VL, VP3VL	-6	-5	-4	
Horizontal shift register clock voltage	High	VP1HH, VP2HH	4	6	8	V
	Low	VP1HL, VP2HL	-6	-5	-4	
Summing gate voltage	High	VSGH	4	6	8	V
	Low	VSHL	-6	-5	-4	
Reset gate voltage	High	VRGH	7	8	9	V
	Low	VRGL	-6	0	-	
Transfer gate voltage	High	VTGH	4	6	8	V
	Low	VTGL	-6	-5	-4	
External load resistance	RL	2.0	2.2	2.4	kΩ	

Electrical characteristics [Ta=25 °C, fc=30 MHz, Typ. value in operating conditions table (P.2), unless otherwise noted]

Parameter	Symbol	Min.	Typ.	Max.	Unit
Signal output frequency	fc	-	30	40	MHz
Vertical shift register capacitance	S10200-02-01	-	250	-	pF
	S10201-04-01	-	400	-	
	S10202-08-01/-16-01	-	650	-	
Line rate	S10200-02-01	-	50	-	kHz
	S10201-04-01	-	50	-	
	S10202-08-01	-	50	-	
	S10202-16-01	-	100	-	
Horizontal shift register capacitance	S10200-02-01	-	50	-	pF
	S10201-04-01	-	90	-	
	S10202-08-01/-16-01	-	90	-	
Transfer gate capacitance	S10200-02-01	-	40	-	pF
	S10201-04-01	-	60	-	
	S10202-08-01/-16-01	-	100	-	
Summing gate capacitance	S10200-02-01	-	20	-	pF
	S10201-04-01	-	40	-	
	S10202-08-01/-16-01	-	40	-	
Reset gate capacitance	S10200-02-01	-	20	-	pF
	S10201-04-01	-	40	-	
	S10202-08-01/-16-01	-	40	-	
Charge transfer efficiency*8	CTE	0.99995	0.99999	-	-
DC output level*9	Vout	-	11	-	V
Output impedance*10	Zo	-	150	-	Ω
Output MOSFET supply current/node	Ido	-	8	12	mA
Power consumption*9 *10	P	-	120	-	mW/port

*8: Charge transfer efficiency per pixel, measured at half of the full well capacity

*9: The values depend on the load resistance. (VOD=15 V, Load resistance=2.2 kΩ)

*10: Power consumption of the on-chip amplifier plus load resistance

Electrical and optical characteristics [Ta=25 °C, fc=30 MHz, Typ. value in operating conditions table (P.2), unless otherwise noted]

Parameter	Symbol	Min.	Typ.	Max.	Unit
Saturation output voltage	Vsat	-	FW × Sv	-	V
Full well capacity*11	FW	80	100	120	ke ⁻
CCD node sensitivity	Sv	8.5	9.5	10.5	μV/e ⁻
Dark current*11 *12	DS	-	30	100	e ⁻ /pixel
Readout noise	Nr	-	35	45	e ⁻ rms
Dynamic range	DR	1777	2857	-	-
Photoresponse nonuniformity*13	PRNU	-	±3	±10	%
Spectral response range	λ	-	200 to 1100	-	nm

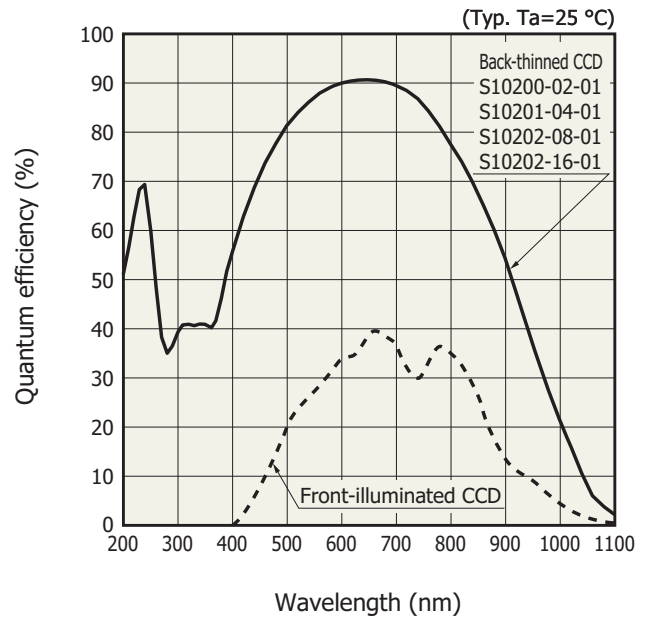
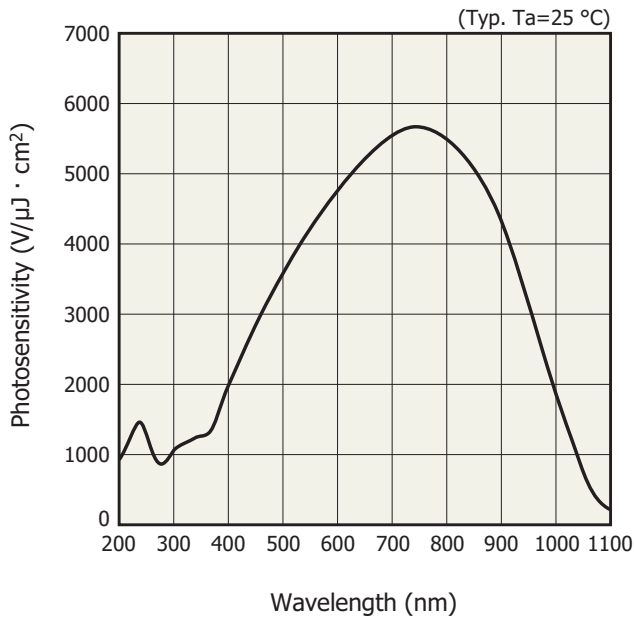
*11: TDI mode

*12: Line rate 50 kHz, accumulated dark signal after 128-stage transfer

*13: Measured at half of the full well capacity, using LED light (peak emission wavelength: 660 nm), in TDI mode

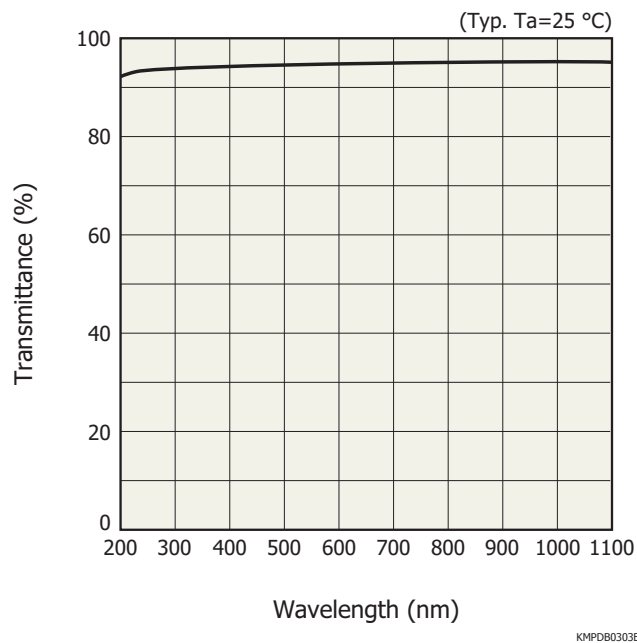
$$\text{Photoresponse nonuniformity (PRNU)} = \frac{\text{Fixed pattern noise (peak to peak)}}{\text{Signal}} \times 100 [\%]$$

Spectral response (without window)*14



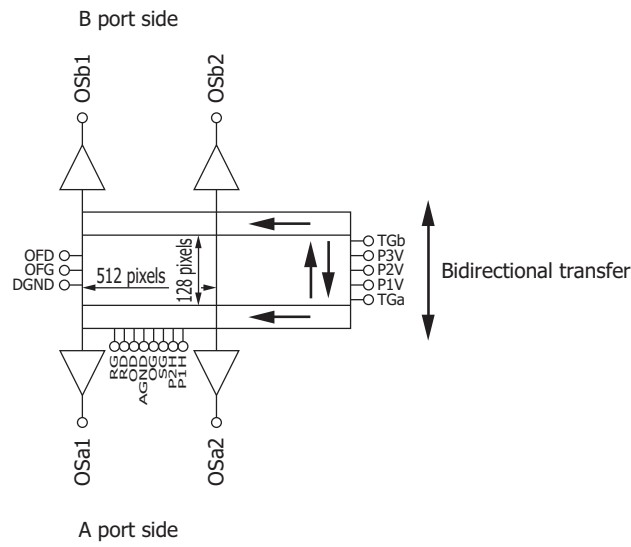
*14: Spectral response with quartz window is decreased according to the spectral transmittance characteristics of window material.

Spectral transmittance characteristics of window material



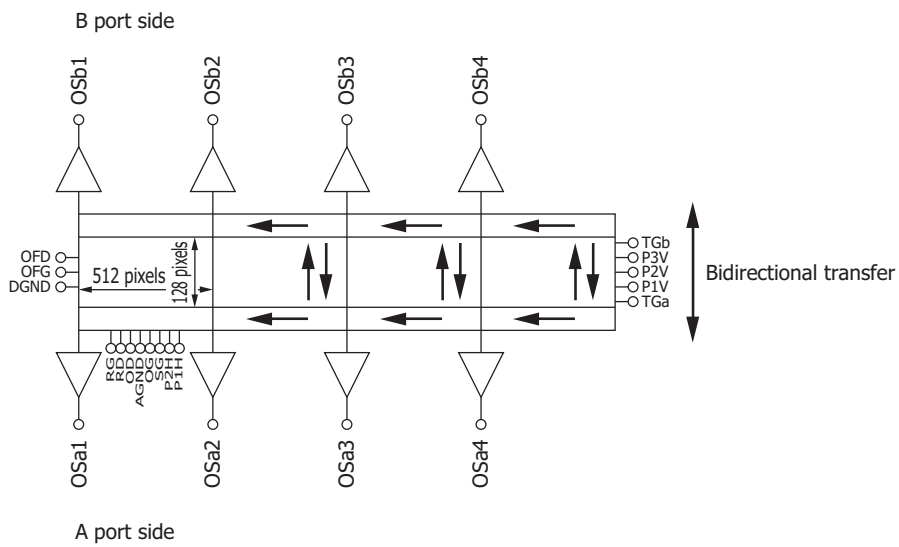
Sensor structure

S10200-02-01



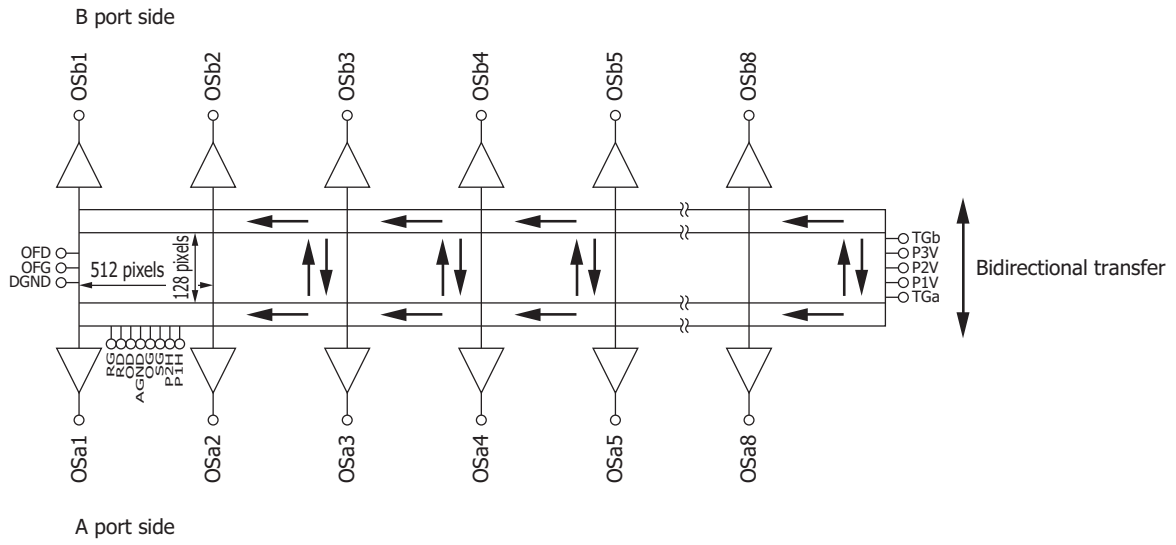
KAPDC0251EA

S10201-04-01



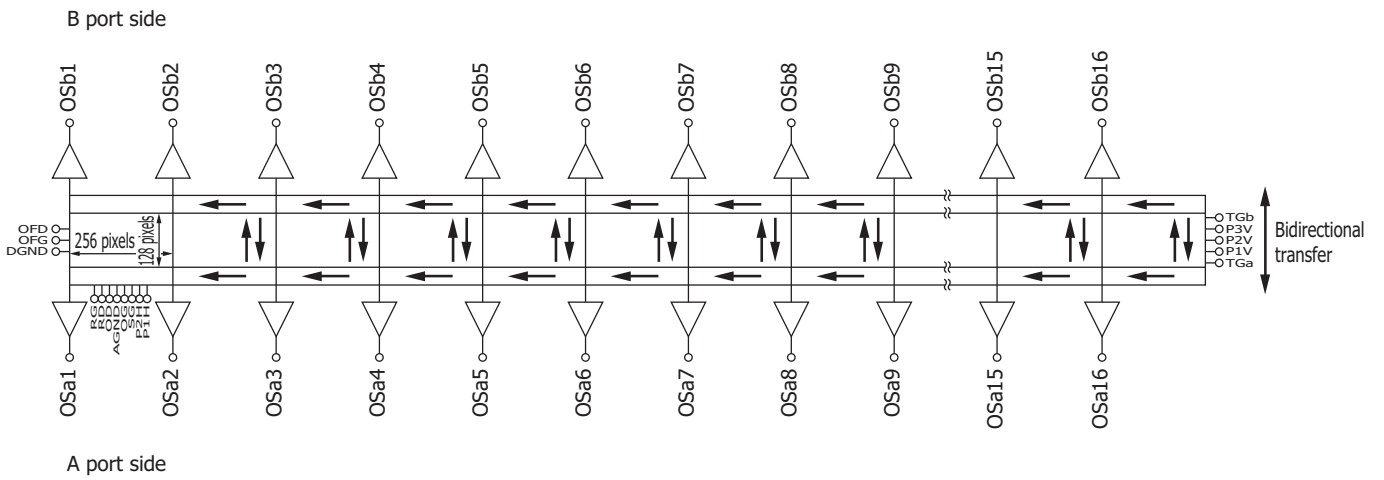
KMPDC0260EA

S10202-08-01



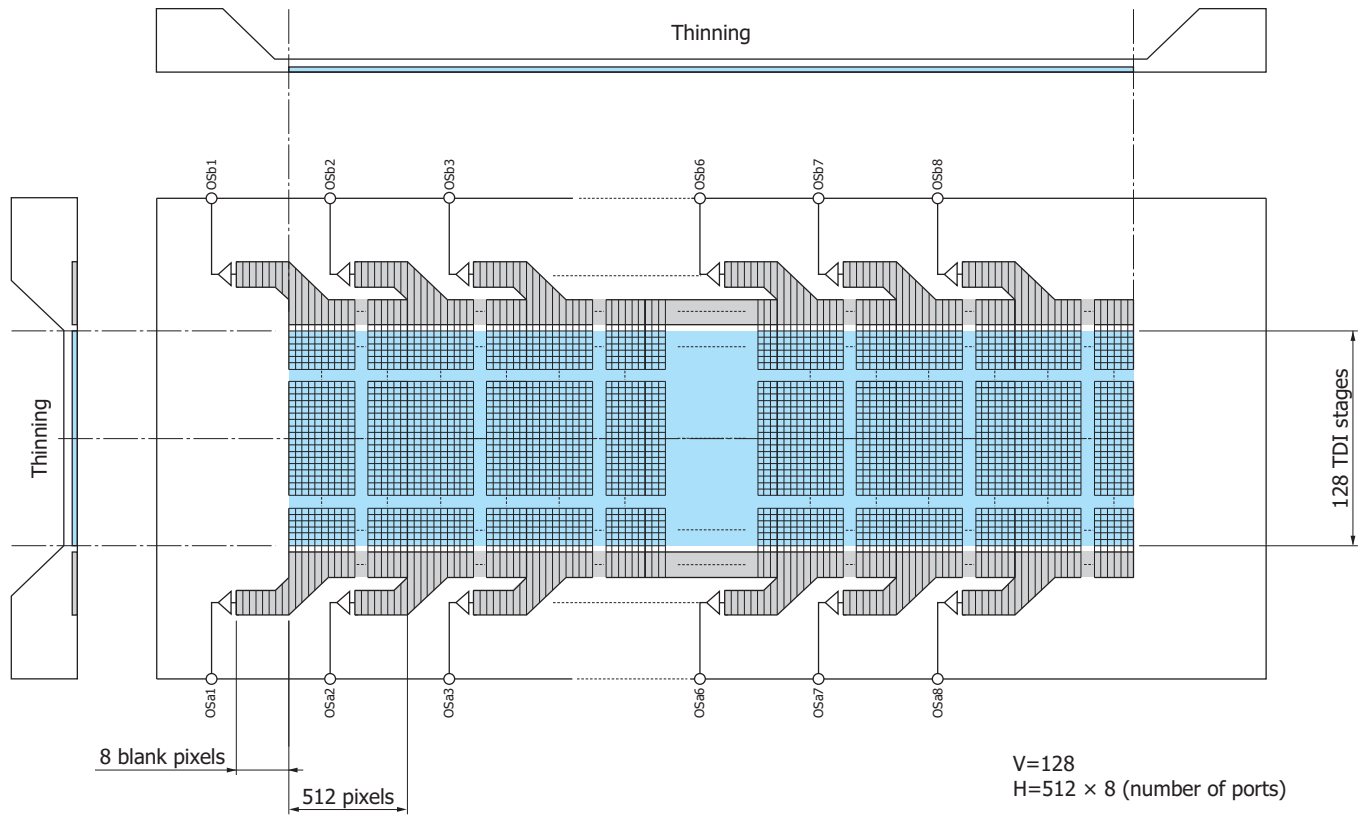
KMPDC0261EA

S10202-16-01



KMPDC0262EA

Device structure (typical example: S10202-08-01, conceptual drawing of top view)



Note: When viewed from the direction of the incident light, the horizontal shift register is covered with a thick silicon layer (dead layer). However, long-wavelength light passes through the silicon dead layer and may possibly be detected by the horizontal shift register. To prevent this, provide light shield on that area as needed.

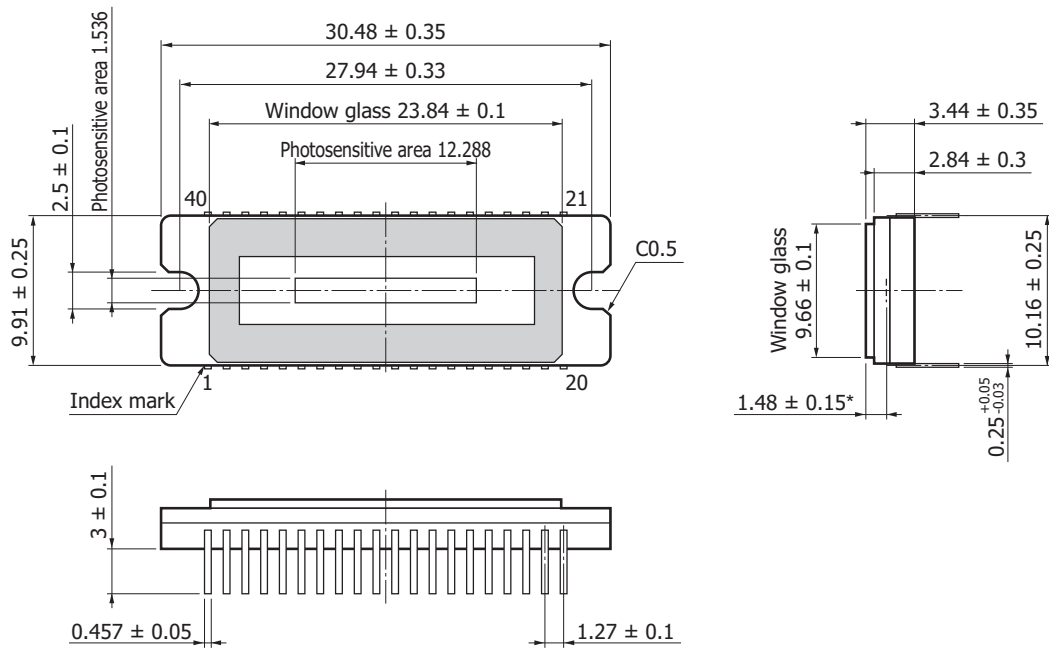
KMPDC0252EB

Parameter		Symbol	Min.	Typ.	Max.	Unit
P1V, 2V, 3V, TG	Pulse width	Tpww	120	770	-	ns
	Rise and fall times	Tprv, Tpfv	2	10	-	ns
	Overlap time	Tovrv	30	300	-	ns
P1H, P2H	Pulse width*15	Tpwh	12.5	16.5	-	ns
	Rise and fall times*15	Tprh, Tpfh	3	6	-	ns
	Duty ratio*15	-	-	50	-	%
SG	Pulse width	Tpws	12.5	16.5	-	ns
	Rise and fall times	Tprs, Tpfs	2	4	-	ns
	Duty ratio	-	-	50	-	%
RG	Pulse width	Tpwr	5	6	-	ns
	Rise and fall times	Tpr, Tprf	1	2	-	ns
TG - P1H	Overlap time	Tovr	30	1000	-	ns

*15: Symmetrical clock pulses should be overlapped at 50% of maximum pulse amplitude.

Dimensional outlines (unit: mm)

S10200-02-01



* Distance from upper surface of window to photosensitive surface

KMPDA0218EC

Pin connections

S10200-02-01				S10201-04-01			
Pin no.	Symbol	Function	Remark	Pin no.	Symbol	Function	Remark
1	P2V	CCD vertical register clock-2		1	P2V	CCD vertical register clock-2	
2	P3V	CCD vertical register clock-3		2	P3V	CCD vertical register clock-3	
3	P1V	CCD vertical register clock-1		3	P1V	CCD vertical register clock-1	
4	TGa	Transfer gate-a		4	TGa	Transfer gate-a	
5	SSD	Digital GND	GND	5	SSD	Digital GND	GND
6	NC	No connection		6	OSa1	Output transistor source-a1	RL=2.2 kΩ
7	SSA	Analog GND	GND	7	SSA	Analog GND	GND
8	OSa1	Output transistor source-a 1	RL=2.2 kΩ	8	OSa2	Output transistor source-a2	RL=2.2 kΩ
9	OD1	Output drain-1	+15 V	9	OD1	Output drain-1	+15 V
10	OSa2	Output transistor source-a 2	RL=2.2 kΩ	10	OSa3	Output transistor source-a3	RL=2.2 kΩ
11	NC	No connection		11	OD3	Output drain-3	+15 V
12	NC	No connection		12	OSa4	Output transistor source-a4	RL=2.2 kΩ
13	OG	Output gate	+6 V	13	OG	Output gate	+6 V
14	RD	Reset drain	+14 V	14	RD	Reset drain	+14 V
15	OFD	Overflow drain	+9 V	15	OFD	Overflow drain	+9 V
16	SSD	Digital GND	GND	16	SSD	Digital GND	GND
17	RGa	Reset gate-a		17	RGa	Reset gate-a	
18	SGa	Summing gate-a		18	SGa	Summing gate-a	
19	P1Ha	CCD horizontal register-a clock-1		19	P1Ha	CCD horizontal register-a clock-1	
20	P2Ha	CCD horizontal register-a clock-2		20	P2Ha	CCD horizontal register-a clock-2	
21	P2Hb	CCD horizontal register-b clock-2		21	P2Hb	CCD horizontal register-b clock-2	
22	P1Hb	CCD horizontal register-b clock-1		22	P1Hb	CCD horizontal register-b clock-1	
23	SGb	Summing gate-b		23	SGb	Summing gate-b	
24	RGb	Reset gate-b		24	RGb	Reset gate-b	
25	SSD	Digital GND	GND	25	SSD	Digital GND	GND
26	OFG	Overflow gate	+5 V	26	OFG	Overflow gate	+5 V
27	RD	Reset drain	+14 V	27	RD	Reset drain	+14 V
28	OG	Output gate	+6 V	28	OG	Output gate	+6 V
29	NC	No connection		29	OSb4	Output transistor source-b4	RL=2.2 kΩ
30	NC	No connection		30	OD4	Output drain-4	+15 V
31	OSb2	Output transistor source-b2	RL=2.2 kΩ	31	OSb3	Output transistor source-b3	RL=2.2 kΩ
32	OD2	Output drain-2	+15 V	32	OD2	Output drain-2	+15 V
33	OSb1	Output transistor source-b1	RL=2.2 kΩ	33	OSb2	Output transistor source-b2	RL=2.2 kΩ
34	SSA	Analog GND	GND	34	SSA	Analog GND	GND
35	NC	No connection		35	OSb1	Output transistor source-b1	RL=2.2 kΩ
36	SSD	Digital GND	GND	36	SSD	Digital GND	GND
37	TGb	Transfer gate-b		37	TGb	Transfer gate-b	
38	P1V	CCD vertical register clock-1		38	P1V	CCD vertical register clock-1	
39	P3V	CCD vertical register clock-3		39	P3V	CCD vertical register clock-3	
40	P2V	CCD vertical register clock-2		40	P2V	CCD vertical register clock-2	

S10202-08-01							
Pin no.	Symbol	Function	Remark	Pin no.	Symbol	Function	Remark
1	P1Ha1	CCD horizontal register-a1 clock-1		51	P1Hb2	CCD horizontal register-b2 clock-1	
2	P2Ha1	CCD horizontal register-a1 clock-2		52	P2Hb2	CCD horizontal register-b2 clock-2	
3	SGa1	Summing gate-a1		53	SGb2	Summing gate-b2	
4	RGa1	Reset gate-a1		54	RGB2	Reset gate-b2	
5	SSD	Digital GND	GND	55	SSD	Digital GND	GND
6	SSA	Analog GND	GND	56	SSA	Analog GND	GND
7	OFG	Overflow gate	+6 V	57	OFG	Overflow gate	+5 V
8	OSa1	Output transistor source-a1	RL=2.2 kΩ	58	NC	No connection	
9	OFD	Overflow drain	+9 V	59	OFD	Overflow drain	+9 V
10	NC	No connection		60	OSb8	Output transistor source-b8	RL=2.2 kΩ
11	RD	Reset drain	+14 V	61	RD	Reset drain	+14 V
12	OSa2	Output transistor source-a2	RL=2.2 kΩ	62	NC	No connection	
13	OG	Output gate	+6 V	63	OG	Output gate	+6 V
14	NC	No connection		64	OSb7	Output transistor source-b7	RL=2.2 kΩ
15	OD1	Output drain-1	+15 V	65	NC	No connection	
16	OSa3	Output transistor source-a3	RL=2.2 kΩ	66	NC	No connection	
17	NC	No connection		67	OD8	Output drain-8	+15 V
18	NC	No connection		68	OSb6	Output transistor source-b6	RL=2.2 kΩ
19	OD3	Output drain-3	+15 V	69	NC	No connection	
20	OSa4	Output transistor source-a4	RL=2.2 kΩ	70	NC	No connection	
21	NC	No connection		71	OD6	Output drain-6	+15 V
22	NC	No connection		72	OSb5	Output transistor source-b5	RL=2.2 kΩ
23	SSD	Digital GND	GND	73	SSD	Digital GND	GND
24	TGa	Transfer gate-a		74	P1V	CCD vertical register clock-1	
25	P2V	CCD vertical register clock-2		75	P3V	CCD vertical register clock-3	
26	P3V	CCD vertical register clock-3		76	P2V	CCD vertical register clock-2	
27	P1V	CCD vertical register clock-1		77	TGb	Transfer gate-b	
28	SSD	Digital GND	GND	78	SSD	Digital GND	GND
29	OSa5	Output transistor source-a5	RL=2.2 kΩ	79	NC	No connection	
30	OD5	Output drain-5	+15 V	80	NC	No connection	
31	NC	No connection		81	OSb4	Output transistor source-b4	RL=2.2 kΩ
32	NC	No connection		82	OD4	Output drain-4	+15 V
33	OSa6	Output transistor source-a6	RL=2.2 kΩ	83	NC	No connection	
34	OD7	Output drain-7	+15 V	84	NC	No connection	
35	NC	No connection		85	OSb3	Output transistor source-b3	RL=2.2 kΩ
36	NC	No connection		86	OD2	Output drain-2	+15 V
37	OSa7	Output transistor source-a7	RL=2.2 kΩ	87	NC	No connection	
38	OG	Output gate	+6 V	88	OG	Output gate	+6 V
39	NC	No connection		89	OSb2	Output transistor source-b2	RL=2.2 kΩ
40	RD	Reset drain	+14 V	90	RD	Reset drain	+14 V
41	OSa8	Output transistor source-a8	RL=2.2 kΩ	91	NC	No connection	
42	OFD	Overflow drain	+9 V	92	OFD	Overflow drain	+9 V
43	NC	No connection		93	OSb1	Output transistor source-b1	RL=2.2 kΩ
44	OFG	Overflow gate	+5 V	94	OFG	Overflow gate	+5 V
45	SSA	Analog GND	GND	95	SSA	Analog GND	GND
46	SSD	Digital GND	GND	96	SSD	Digital GND	GND
47	RGa2	Reset gate-a2		97	RGB1	Reset gate-b1	
48	SGa2	Summing gate-a2		98	SGb1	Summing gate-b1	
49	P2Ha2	CCD horizontal register-a2 clock-2		99	P2Hb1	CCD horizontal register-b1 clock-2	
50	P1Ha2	CCD horizontal register-a2 clock-1		100	P1Hb1	CCD horizontal register-b1 clock-1	

S10202-16-01							
Pin no.	Symbol	Function	Remark	Pin no.	Symbol	Function	Remark
1	P1Ha1	CCD horizontal register-a1 clock-1		51	P1Hb2	CCD horizontal register-b2 clock-1	
2	P2Ha1	CCD horizontal register-a1 clock-2		52	P2Hb2	CCD horizontal register-b2 clock-2	
3	SGa1	Summing gate-a1		53	SGb2	Summing gate-b2	
4	RGa1	Reset gate-a1		54	RGB2	Reset gate-b2	
5	SSD	Digital GND	GND	55	SSD	Digital GND	GND
6	SSA	Analog GND	GND	56	SSA	Analog GND	GND
7	OFG	Overflow gate	+5 V	57	OFG	Overflow gate	+5 V
8	OSa1	Output transistor source-a1	RL=2.2 kΩ	58	OSb16	Output transistor source-b16	RL=2.2 kΩ
9	OFD	Overflow drain	+9 V	59	OFD	Overflow drain	+9 V
10	OSa2	Output transistor source-a2	RL=2.2 kΩ	60	OSb15	Output transistor source-b15	RL=2.2 kΩ
11	RD	Reset drain	+14 V	61	RD	Reset drain	+14 V
12	OSa3	Output transistor source-a3	RL=2.2 kΩ	62	OSb14	Output transistor source-b14	RL=2.2 kΩ
13	OG	Output gate	+6 V	63	OG	Output gate	+6 V
14	OSa4	Output transistor source-a4	RL=2.2 kΩ	64	OSb13	Output transistor source-b13	RL=2.2 kΩ
15	OD1	Output drain-1	+15 V	65	OD16	Output drain-16	+15 V
16	OSa5	Output transistor source-a5	RL=2.2 kΩ	66	OSb12	Output transistor source-b12	RL=2.2 kΩ
17	OD2	Output drain-2	+15 V	67	OD15	Output drain-15	+15 V
18	OSa6	Output transistor source-a6	RL=2.2 kΩ	68	OSb11	Output transistor source-b11	RL=2.2 kΩ
19	OD5	Output drain-5	+15 V	69	OD12	Output drain-12	+15 V
20	OSa7	Output transistor source-a7	RL=2.2 kΩ	70	OSb10	Output transistor source-b10	RL=2.2 kΩ
21	OD6	Output drain-6	+15 V	71	OD11	Output drain-11	+15 V
22	OSa8	Output transistor source-a8	RL=2.2 kΩ	72	OSb9	Output transistor source-b9	RL=2.2 kΩ
23	SSD	Digital GND	GND	73	SSD	Digital GND	GND
24	TGa	Transfer gate-a		74	P1V	CCD vertical register clock-1	
25	P2V	CCD vertical register clock-2		75	P3V	CCD vertical register clock-3	
26	P3V	CCD vertical register clock-3		76	P2V	CCD vertical register clock-2	
27	P1V	CCD vertical register clock-1		77	TGb	Transfer gate-b	
28	SSD	Digital GND	GND	78	SSD	Digital GND	GND
29	OSa9	Output transistor source-a9	RL=2.2 kΩ	79	OSb8	Output transistor source-b8	RL=2.2 kΩ
30	OD9	Output drain-9	+15 V	80	OD8	Output drain-8	+15 V
31	OSa10	Output transistor source-a10	RL=2.2 kΩ	81	OSb7	Output transistor source-b7	RL=2.2 kΩ
32	OD10	Output drain-10	+15 V	82	OD7	Output drain-7	+15 V
33	OSa11	Output transistor source-a11	RL=2.2 kΩ	83	OSb6	Output transistor source-b6	RL=2.2 kΩ
34	OD13	Output drain-13	+15 V	84	OD4	Output drain-4	+15 V
35	OSa12	Output transistor source-a12	RL=2.2 kΩ	85	OSb5	Output transistor source-b5	RL=2.2 kΩ
36	OD14	Output drain-14	+15 V	86	OD3	Output drain-3	+15 V
37	OSa13	Output transistor source-a13	RL=2.2 kΩ	87	OSb4	Output transistor source-b4	RL=2.2 kΩ
38	OG	Output gate	+6 V	88	OG	Output gate	+6 V
39	OSa14	Output transistor source-a14	RL=2.2 kΩ	89	OSb3	Output transistor source-b3	RL=2.2 kΩ
40	RD	Reset drain	+14 V	90	RD	Reset drain	+14 V
41	OSa15	Output transistor source-a15	RL=2.2 kΩ	91	OSb2	Output transistor source-b2	RL=2.2 kΩ
42	OFD	Overflow drain	+9 V	92	OFD	Overflow drain	+9 V
43	OSa16	Output transistor source-a16	RL=2.2 kΩ	93	OSb1	Output transistor source-b1	RL=2.2 kΩ
44	OFG	Overflow gate	+5 V	94	OFG	Overflow gate	+5 V
45	SSA	Analog GND	GND	95	SSA	Analog GND	GND
46	SSD	Digital GND	GND	96	SSD	Digital GND	GND
47	RGa2	Reset gate-a2		97	RGB1	Reset gate-b1	
48	SGa2	Summing gate-a2		98	SGb1	Summing gate-b1	
49	P2Ha2	CCD horizontal register-a2 clock-2		99	P2Hb1	CCD horizontal register-b1 clock-2	
50	P1Ha2	CCD horizontal register-a2 clock-1		100	P1Hb1	CCD horizontal register-b1 clock-1	

⚠ Precautions (Electrostatic countermeasures)

- Handle these sensors with bare hands or wearing cotton gloves. In addition, wear anti-static clothing or use a wrist band with an earth ring, in order to prevent electrostatic damage due to electrical charges from friction.
- Avoid directly placing these sensors on a work-desk, etc. that may carry an electrostatic charge.
- Provide ground lines or ground connection with the work-floor, work-desk and work-bench to allow static electricity to discharge.
- Ground the tools used to handle these sensors, such as tweezers and soldering irons.

It is not always necessary to provide all the electrostatic measures stated above. Implement these measures according to the amount of damage that occurs.

⚠ Related information

www.hamamatsu.com/sp/ssd/doc_en.html

■ Precautions

- Disclaimer
- Image sensors/Precautions

TDI camera C10000 series

The TDI camera C10000 series is useful in a wide range of imaging applications that require both high speed and high sensitivity, including in-line monitoring and inspection.

■ Product information

www.hamamatsu.com/all/en/C10000-801.html



C10000-801 (With S10201-04-01)



C10000-A01 (With S10201-04-01)

Electrical and optical characteristics listed in the datasheet are the values when used under typical operating conditions. We recommend using the product under typical operating conditions. Product characteristics vary with operating conditions. Operating conditions specified in the datasheet show the adjustment range. They must be adjusted within the specified range.

Information described in this material is current as of October 2016.

Product specifications are subject to change without prior notice due to improvements or other reasons. This document has been carefully prepared and the information contained is believed to be accurate. In rare cases, however, there may be inaccuracies such as text errors. Before using these products, always contact us for the delivery specification sheet to check the latest specifications.

The product warranty is valid for one year after delivery and is limited to product repair or replacement for defects discovered and reported to us within that one year period. However, even if within the warranty period we accept absolutely no liability for any loss caused by natural disasters or improper product use. Copying or reprinting the contents described in this material in whole or in part is prohibited without our prior permission.

HAMAMATSU

www.hamamatsu.com

HAMAMATSU PHOTONICS K.K., Solid State Division

1126-1 Ichino-cho, Higashi-ku, Hamamatsu City, 435-8558 Japan, Telephone: (81) 53-434-3311, Fax: (81) 53-434-5184

U.S.A.: Hamamatsu Corporation: 360 Foothill Road, Bridgewater, N.J. 08807, U.S.A., Telephone: (1) 908-231-0960, Fax: (1) 908-231-1218

Germany: Hamamatsu Photonics Deutschland GmbH: Arzbergerstr. 10, D-82211 Herrsching am Ammersee, Germany, Telephone: (49) 8152-375-0, Fax: (49) 8152-265-8

France: Hamamatsu Photonics France S.A.R.L.: 19, Rue du Saule Trapu, Parc du Moulin de Massy, 91882 Massy Cedex, France, Telephone: 33-(1) 69 53 71 00, Fax: 33-(1) 69 53 71 10

United Kingdom: Hamamatsu Photonics UK Limited: 2 Howard Court, 10 Tewin Road, Welwyn Garden City, Hertfordshire AL7 1BW, United Kingdom, Telephone: (44) 1707-294888, Fax: (44) 1707-325777

North Europe: Hamamatsu Photonics Norden AB: Torshamnsgatan 35 16440 Kista, Sweden, Telephone: (46) 8-509-031-00, Fax: (46) 8-509-031-01

Italy: Hamamatsu Photonics Italia S.r.l.: Strada della Moia, 1 int. 6, 20020 Arese (Milano), Italy, Telephone: (39) 02-93581733, Fax: (39) 02-93581741

China: Hamamatsu Photonics (China) Co., Ltd.: B1201, Jiaming Center, No.27 Dongsanhuan Beilu, Chaoyang District, Beijing 100020, China, Telephone: (86) 10-6586-6006, Fax: (86) 10-6586-2866